BYC8X-600P

Hyperfast power diode 24 July 2012

Product data sheet

1. **Product profile**

1.1 General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

1.3 Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	SQW; $\delta = 0.5$; $T_h \le 75$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	8	А
Static characte	eristics						
V _F	forward voltage	I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>		-	1.5	1.9	V
Dynamic characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	12	18	ns





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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYC8X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	SQW; δ = 0.5; $T_h \le 75$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	8	А
I _{FRM}	repetitive peak forward current	SQW; δ = 0.5 ; t_p = 25 μ s; $T_h \le 75$ °C	-	16	Α
I _{FSM}	non-repetitive peak forward	SIN; $t_p = 10 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; Fig. 4	-	91	Α
	current	SIN; $t_p = 8.3 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; Fig. 4	-	100	Α
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

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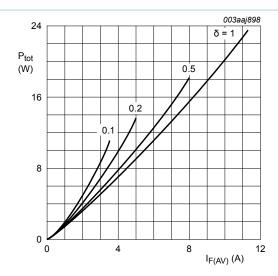


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

 $V_O = 1.581 \text{ V}; \text{ R}_S = 0.043 \Omega$

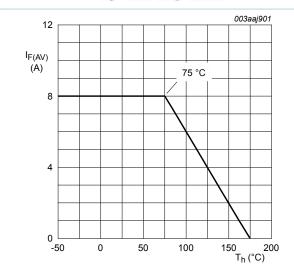


Fig. 3. Average forward current as a function of heatsink temperature; maximum values

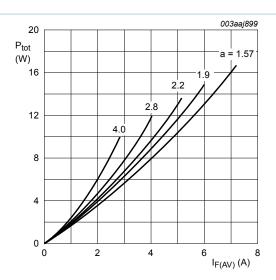


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

V_O = 1.581 V; R_S = 0.043 Ω

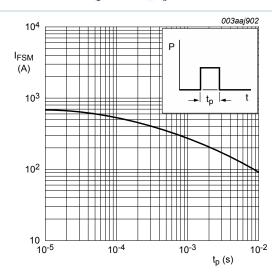


Fig. 4. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance	without heatsink compound	-	-	7.2	K/W
,	from junction to heatsink	with heatsink compound ; Fig. 5	-	-	5.5	K/W

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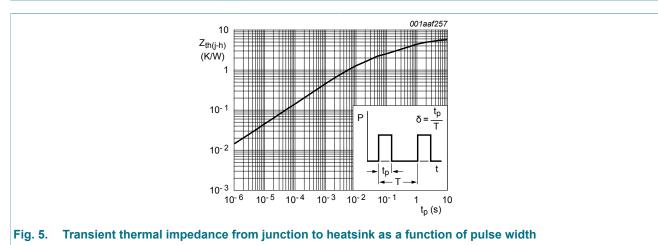
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	60	-	K/W



Isolation characteristics

Isolation characteristics Table 6.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz ; from cathode to external heatsink	-	10	-	pF

Characteristics

Table 7. **Characteristics**

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
Static char	Static characteristics								
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	3.4	V			
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V			
I _R rev	reverse current	V _R = 600 V; T _j = 25 °C	-	-	20	μΑ			
		V _R = 600 V; T _j = 125 °C	-	-	200	μΑ			
Dynamic cl	haracteristics								
Q _r	recovered charge	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	17	-	nC			
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 125 \text{ °C}; \underline{\text{Fig. 7}}$	-	90	-	nC			

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	12	18	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	2.2	A
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 125 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	6	Α

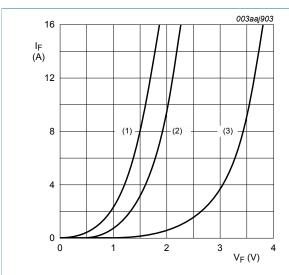


Fig. 6. Forward current as a function of forward voltage

(1) $T_j = 125$ °C; typical values; (2) $T_j = 125$ °C; maximum values; (3) $T_j = 25$ °C; maximum values; $V_O = 1.581$ V; $R_S = 0.043$ Ω

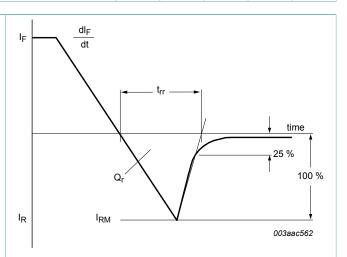


Fig. 7. Reverse recovery definitions; ramp recovery

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8. Package outline

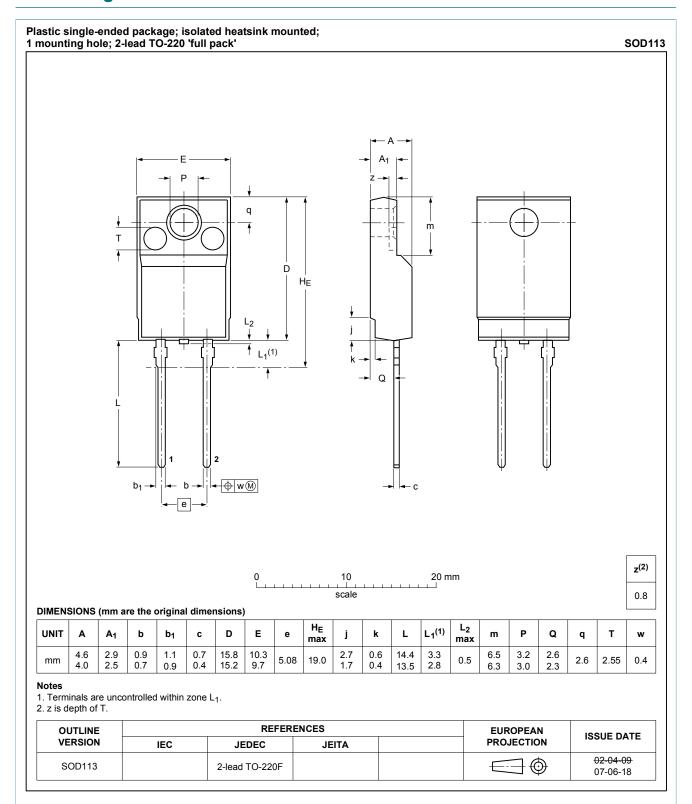


Fig. 8. TO-220F (SOD113)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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